100 V power Schottky rectifier





Features

- · High junction temperature capability
- Low leakage current
- Good trade-off between leakage current and forward voltage drop
- Low thermal resistance
- · High frequency operation
- ECOPACK®2 compliant

Applications

- · Switching diode
- SMPS
- DC/DC converter
- · Telecom power
- · Desktop power supply

Description

This dual diode common cathode Schottky rectifier is suited for high frequency switched mode power supplies.

Packaged in TO-247, the STPS61H100C is optimized for use to enhance the reliability of the application.

Product status			
STPS61H100C			
Product summary			
I _{F(AV)} 2 x 30 A			
V _{RRM}	100 V		
T _{j(max.)}	175 °C		
V _{F(typ.)}	0.63 V		



1 Characteristics

Table 1. Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol	Parameter	Value	Unit		
V_{RRM}	Repetitive peak reverse voltage			100	V
I _{F(RMS)}	Forward rms current			80	Α
	August Sandal Sa	T _c = 150 °C	Per diode	30	_
I _{F(AV)}	Average forward current, δ = 0.5, square wave	T _c = 145 °C	Per device	60	Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			450	Α
P _{ARM}	Repetitive peak avalanche power $t_p = 10 \mu s$, $T_j = 125 °C$			1900	W
T _{stg}	Storage temperature range				°C
Tj	Maximum operating junction temperature (1)			+175	°C

^{1.} $(dP_{tot}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter		Max. value	Unit
D.,	Junction to case	Per diode	0.9	°C/W
$R_{th(j-c)}$		Total	0.6	
R _{th(c)}	Coupling		0.3	°C/W

When the diodes 1 and 2 are used simultaneously: $\Delta T_{j \text{ (diode1)}} = P_{\text{(diode1)}} \times R_{\text{th(j-c)}}$ (per diode) + $P_{\text{(diode2)}} \times R_{\text{th(c)}}$

For more information, please refer to the following application note:

AN5088: Rectifiers thermal management, handling and mounting recommendations

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Doverse legizare gurrent	T _j = 25 °C	$V_R = V_{RRM}$	-	3	16	μA
'R\'	Reverse leakage current	T _j = 125 °C		-	4	16	mA
	Forward voltage drop	T _j = 25 °C	I _F = 30 A	-		0.79	V
V _F ⁽²⁾		T _j = 125 °C		-	0.63	0.67	
VF (-)		T _j = 25 °C	I _F = 60 A	-		0.93	
		T _j = 125 °C		-	0.72	0.78	

- 1. Pulse test: $t_p = 5$ ms, $\delta < 2\%$
- 2. Pulse test: t_p =380 μ s, δ < 2%

To evaluate the conduction losses, use the following equation: P = 0.56 x $I_{F(AV)}$ + 0.0036 x I_{F} 2 (RMS)

For more information, please refer to the following application notes related to the power losses:

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode



1.1 Characteristics (curves)

average forward current (per diode) $P_{F(AV)}(W)$ $\delta = 0.1 \qquad \delta = 0.2 \qquad \delta = 0.5 \qquad \delta = 1.0$ $0 \qquad 15 \qquad 10 \qquad 10$

Figure 1. Average forward power dissipation versus

Figure 2. Average forward current versus ambient temperature (δ = 0.5, per diode)

Figure 3. Normalized avalanche power derating versus pulse duration (T_i= 125 °C)

I_{F(AV)}(A)

15

δ=tp/T

35

30

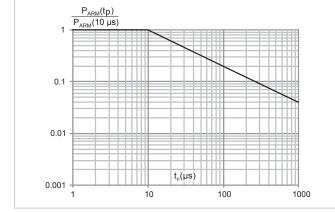


Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

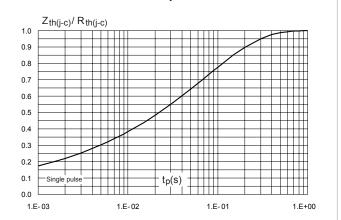




Figure 5. Reverse leakage current versus reverse voltage applied (typical values, per diode)

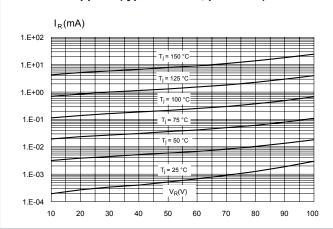
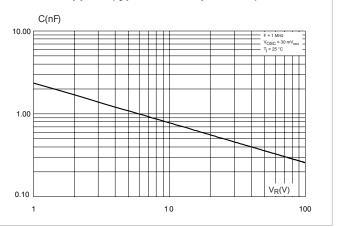
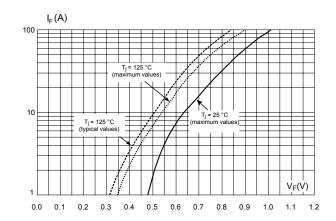


Figure 6. Junction capacitance versus reverse voltage applied (typical values, per diode)









Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 TO-247 package information

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.8 N·m

• Maximum torque value: 1.0 N·m

Figure 8. TO-247 package outline

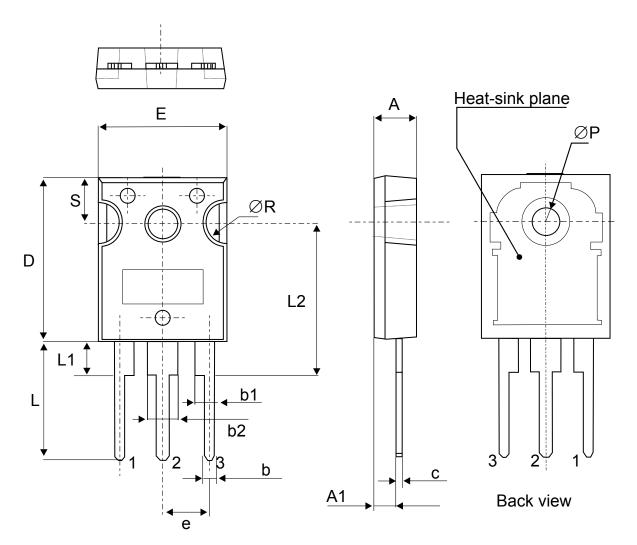




Table 4. TO-247 package mechanical data

		Dimensions						
Ref.		Millimeters			Inches (for reference only)			
	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α	4.85		5.15	0.191		0.203		
A1	2.20		2.60	0.086		0.102		
b	1.00		1.40	0.039		0.055		
b1	2.00		2.40	0.078		0.094		
b2	3.00		3.40	0.118		0.133		
С	0.40		0.80	0.015		0.031		
D	19.85		20.15	0.781		0.793		
Е	15.45		15.75	0.608		0.620		
е	5.30	5.45	5.60	0.209	0.215	0.220		
L	14.20		14.80	0.559		0.582		
L1	3.70		4.30	0.145		0.169		
L2		18.50			0.728			
ØP	3.55		3.65	0.139		0.143		
ØR	4.50		5.50	0.177		0.217		
S	5.30	5.50	5.70	0.209	0.216	0.224		



3 Ordering information

Table 5. Order code

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS61H100CW	STPS61H100CW	TO-247	4.36 g	30	Tube



Revision history

Table 6. Document revision history

Date	Revision	Changes
Oct-2003	1A	Previous version.
Sep-2006	2	Reformatted for internal distribution.
12-Mar-2012	3	Updated package dimension nomenclature and illustration in Table 5. Dimensions of actual package remain unchanged.
09-Aug-2018	4	Updated Table 1. Absolute ratings (limiting values per diode at 25 $^{\circ}$ C, unless otherwise specified) and Figure 3. Normalized avalanche power derating versus pulse duration (T _j = 125 $^{\circ}$ C).



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